

<b>SANYO</b>	No.1404B	<b>2SK427</b>
		N-Channel Junction Silicon FET

**AM Tuner RF Amp Applications**

**Applications**

- AM tuner RF amps and low-noise amps.

**Features**

- Large  $|Y_{fs}|$ .
- Ultralow noise figure.
- Small Crss.

**Absolute Maximum Ratings at Ta = 25°C**

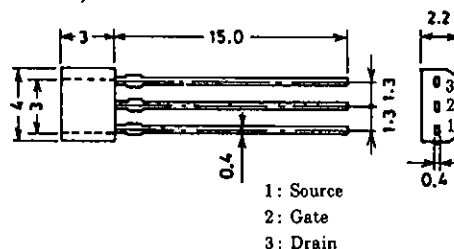
			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	15	V
Gate-to-Drain Voltage	V <sub>GDS</sub>	-15	V
Gate Current	I <sub>G</sub>	10	mA
Drain Current	I <sub>D</sub>	20	mA
Allowable Power Dissipation	P <sub>D</sub>	200	mW
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
G-D Breakdown Voltage	V <sub>(BR)GDS</sub>	I <sub>G</sub> = -10μA, V <sub>DS</sub> = 0	-15			V
Gate Cutoff Current	I <sub>GSS</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = 0			-1.0	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 100μA		-0.5	-1.5	V
Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0	1.2※		12.0※	mA
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0, f = 1kHz	8.0	17		mS
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0, f = 1MHz		7.0		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 0, f = 1MHz		2.0		pF
Noise Figure	NF	V <sub>DS</sub> = 5V, I <sub>D</sub> = 1mA, R <sub>g</sub> = 1kΩ, f = 1kHz		1.5		dB

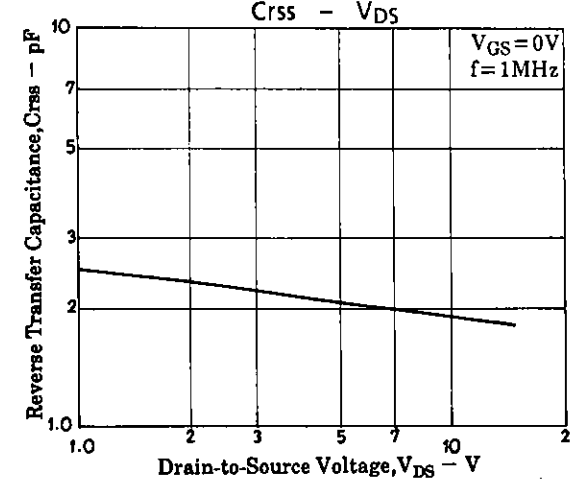
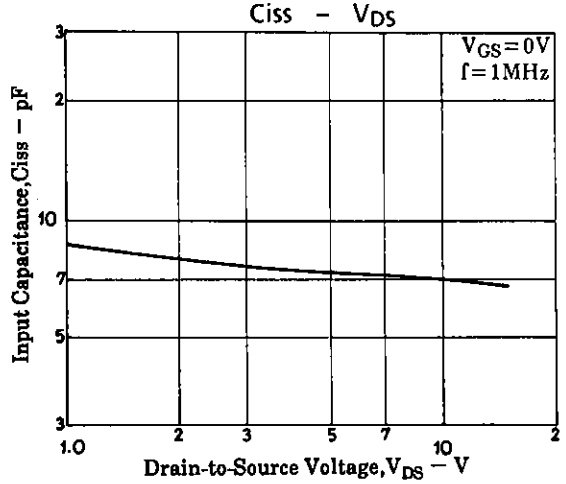
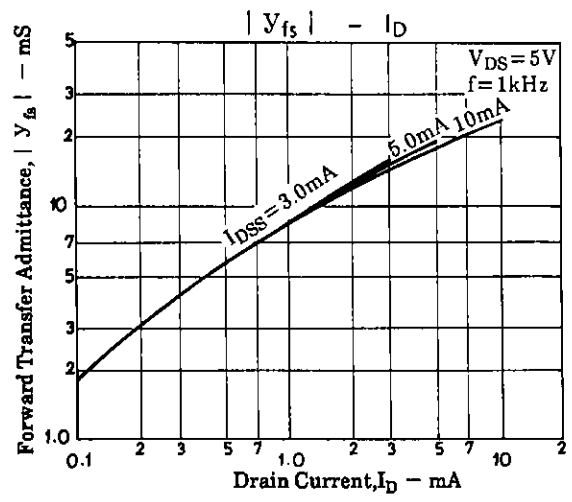
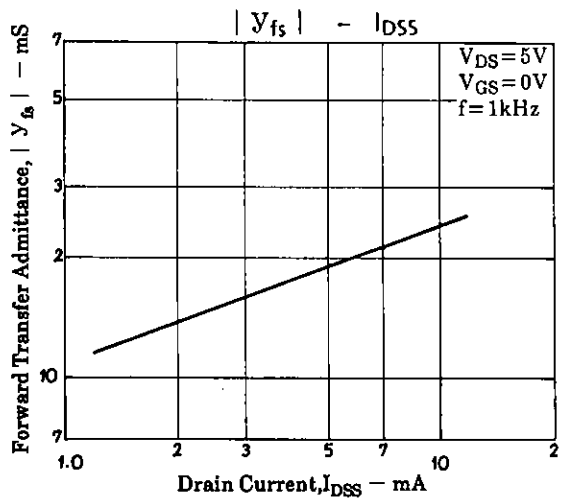
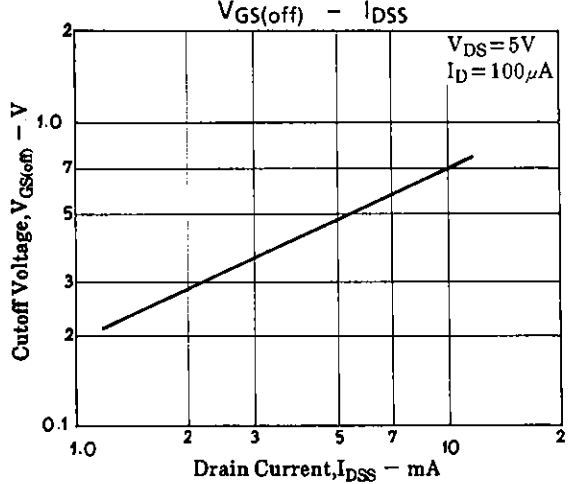
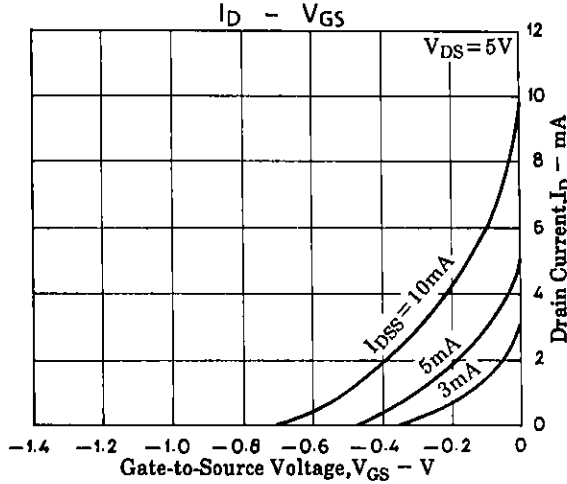
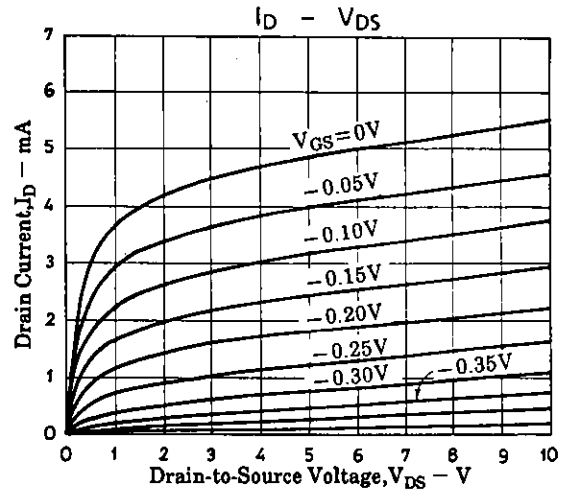
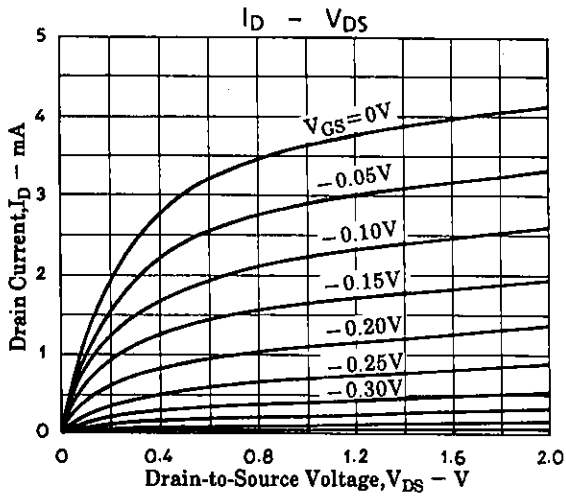
※ : The 2SK427 is classified by I<sub>DSS</sub> as follows : (unit : mA)

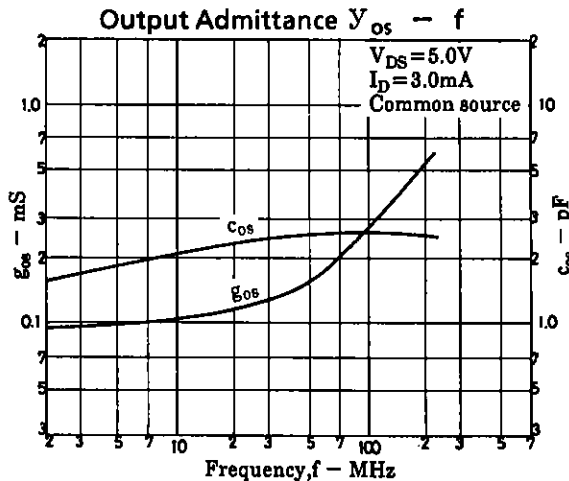
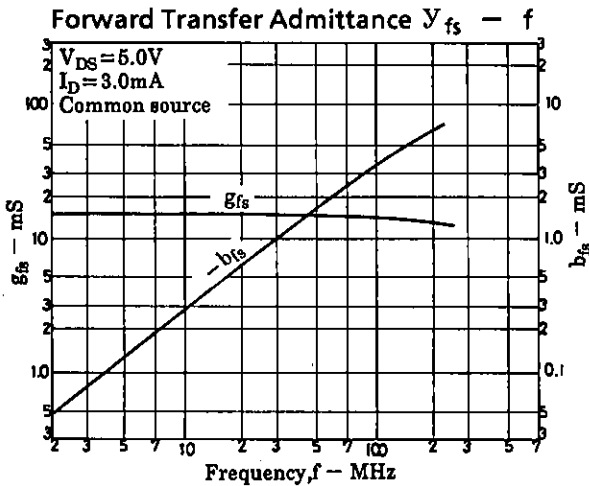
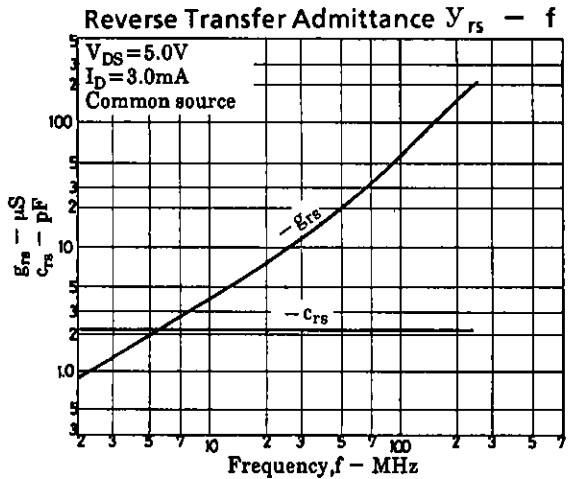
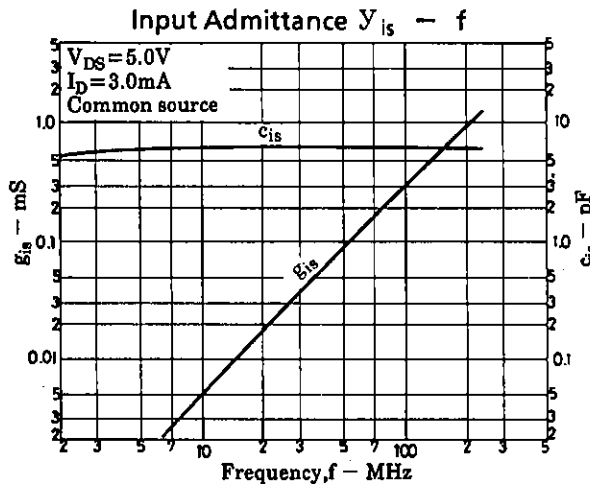
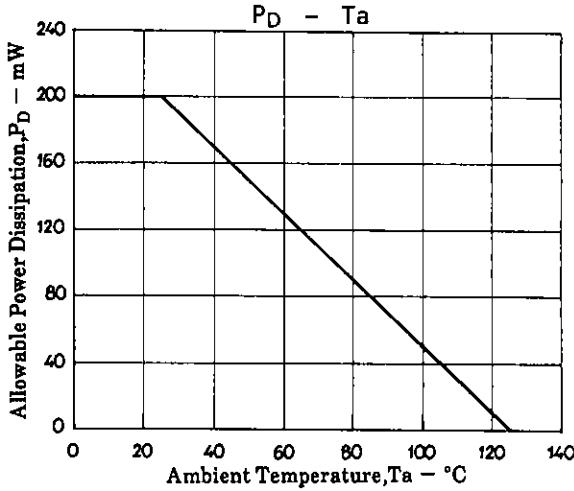
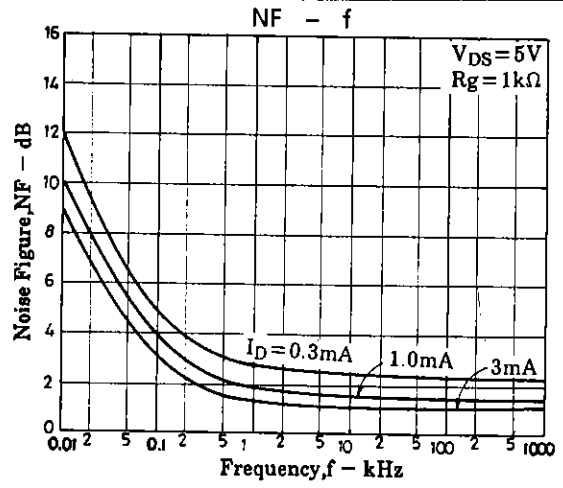
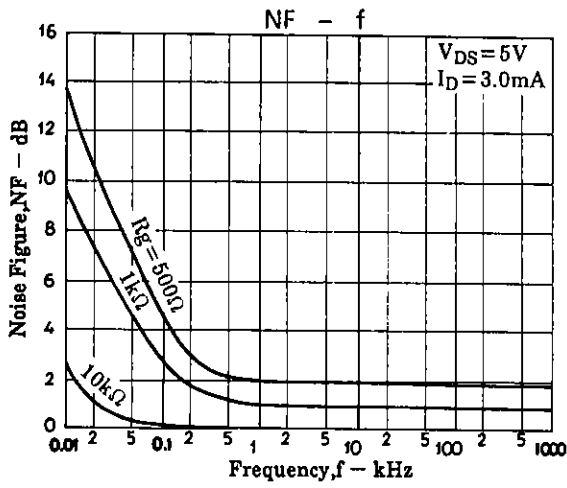
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3.5 S	6.0	5.0 T	8.5	7.3 U	12.0

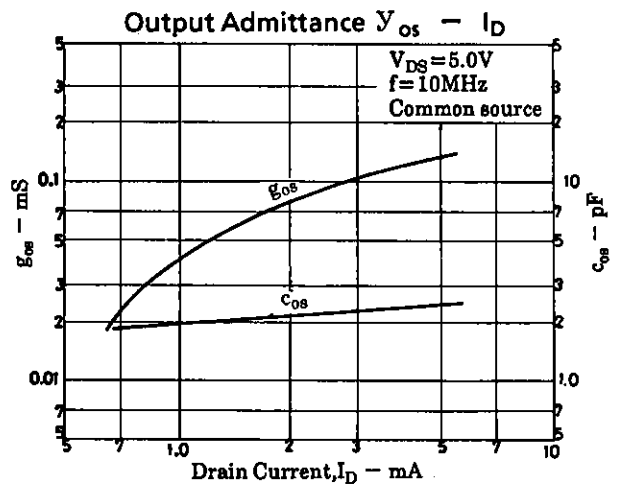
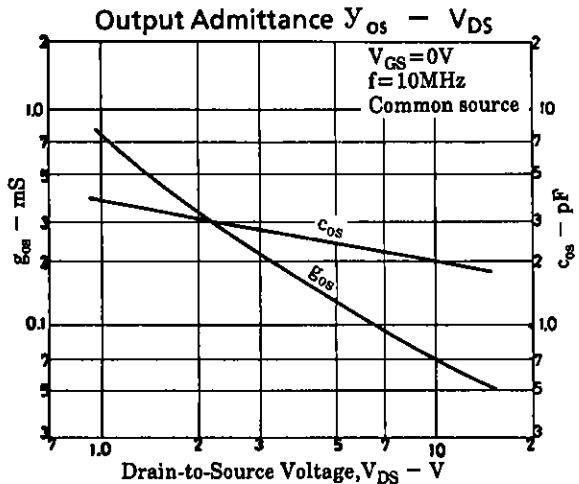
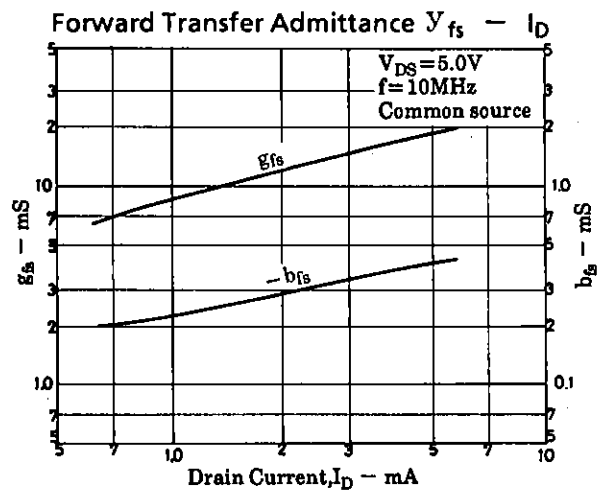
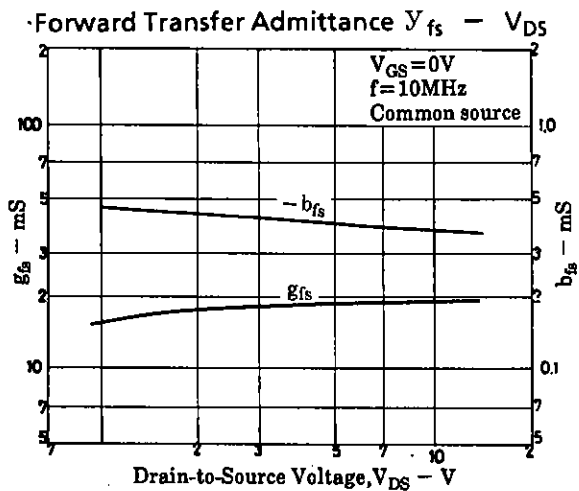
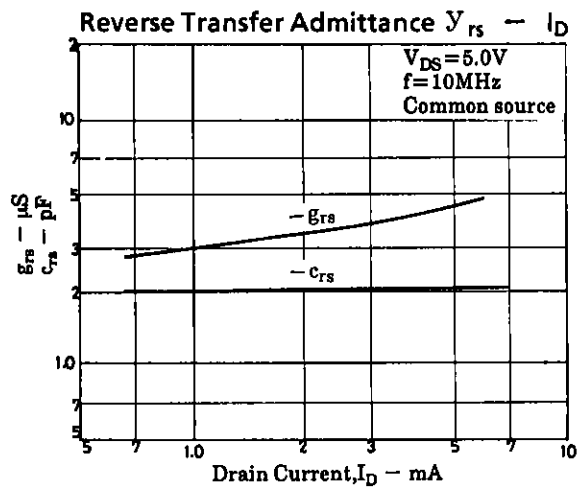
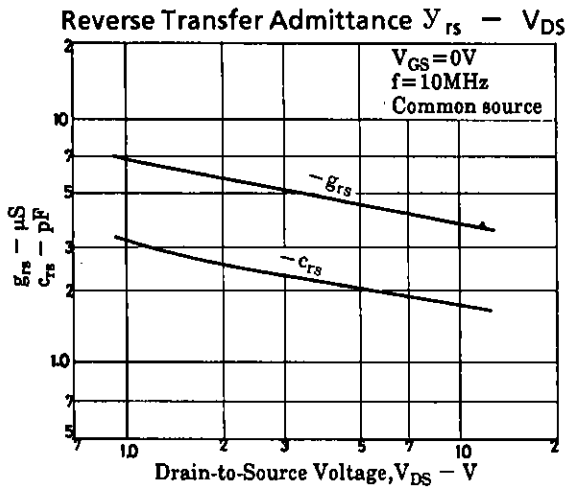
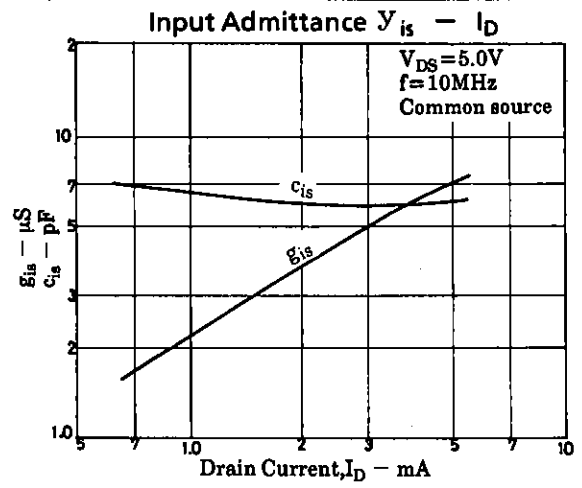
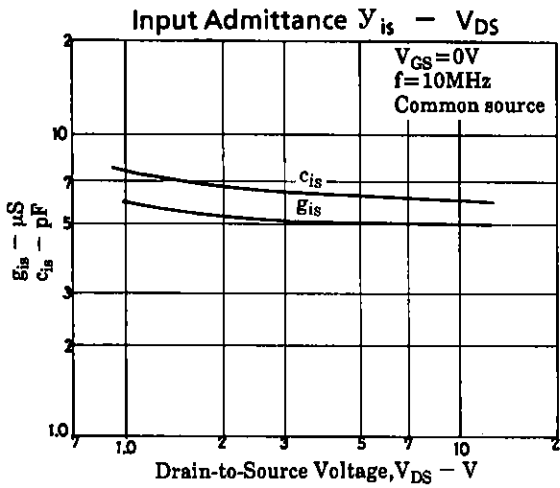
**Package Dimensions 2034A**  
(unit : mm)

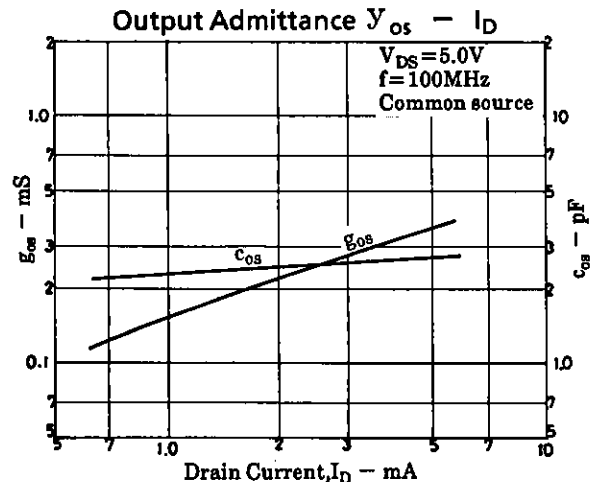
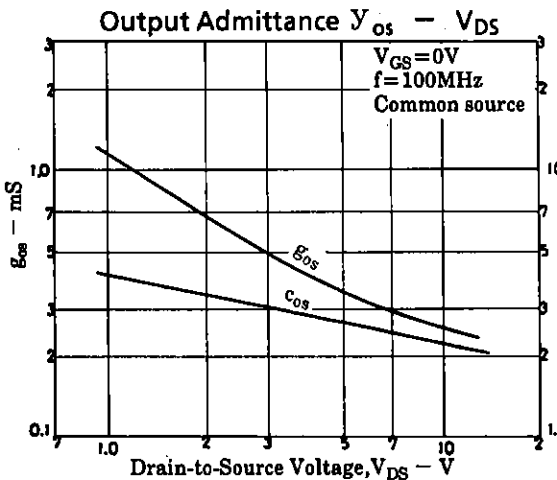
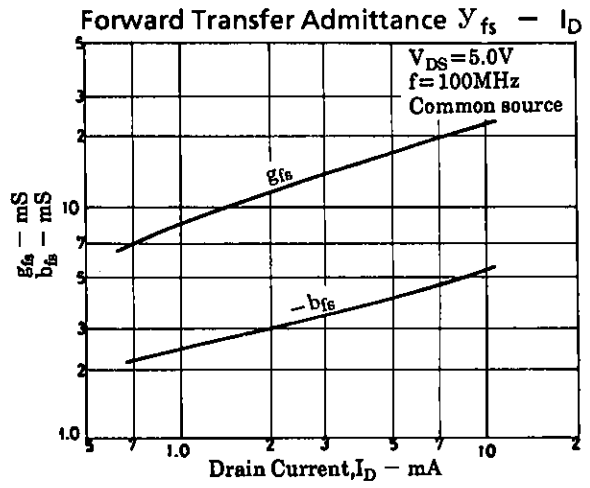
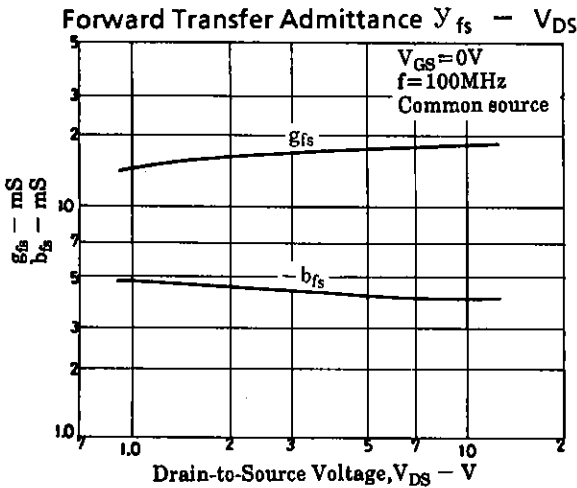
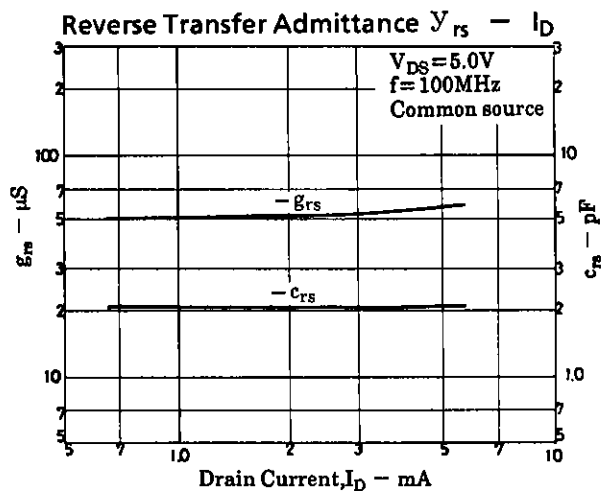
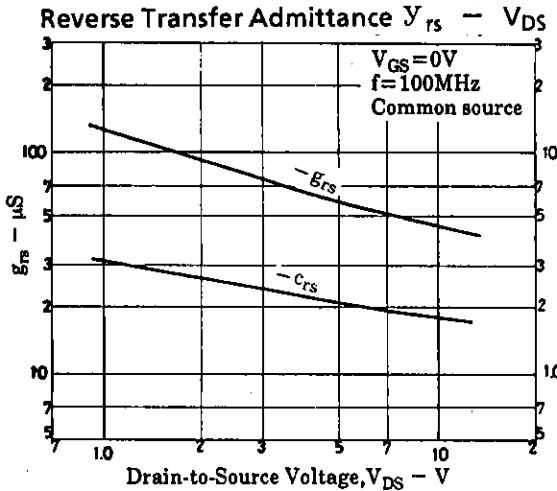
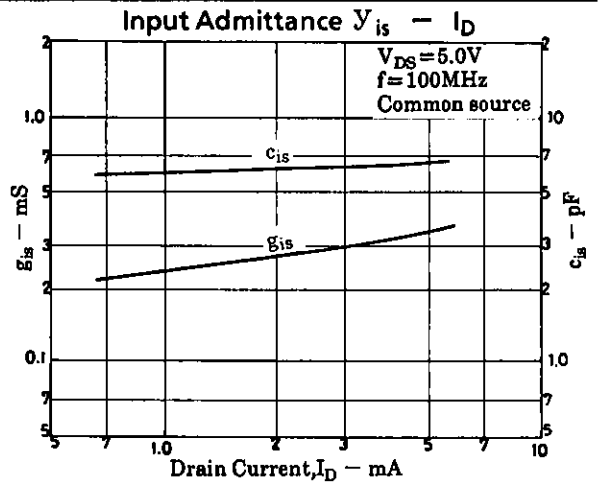
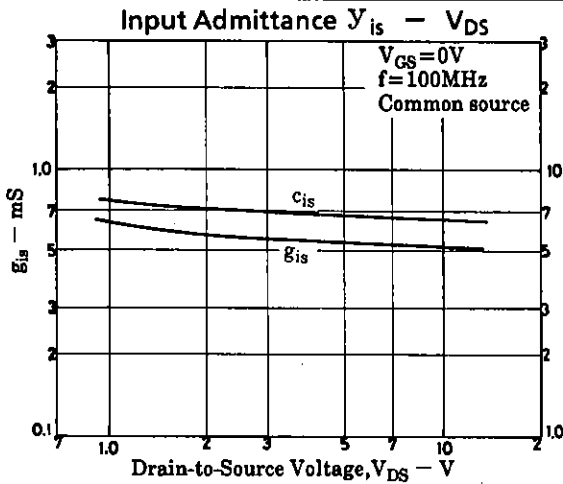
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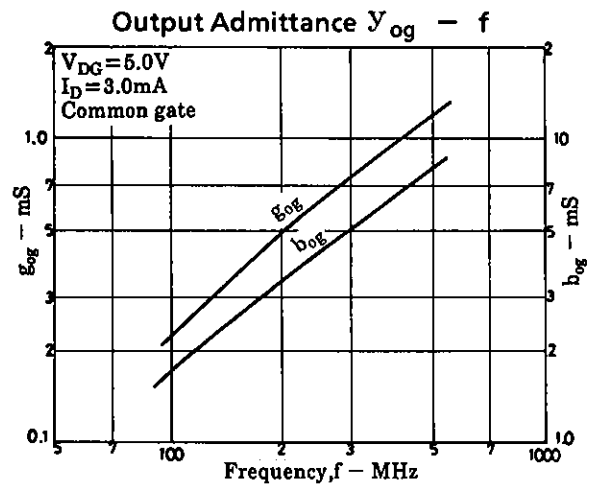
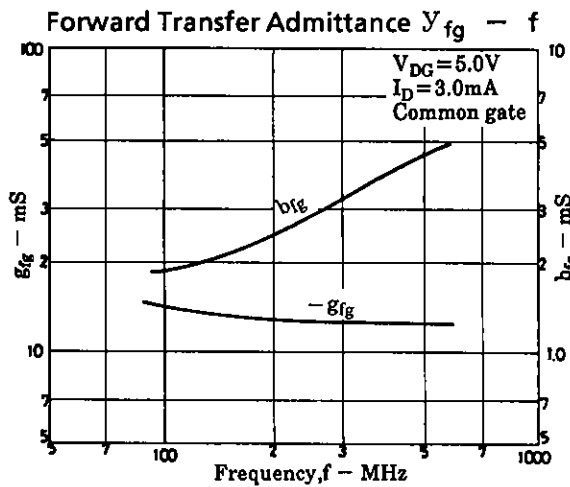
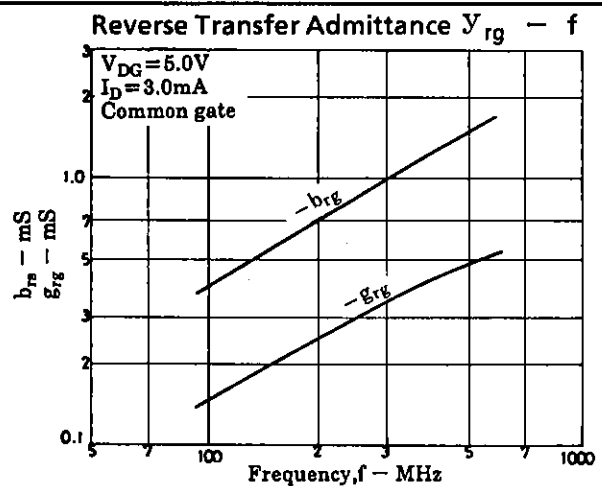
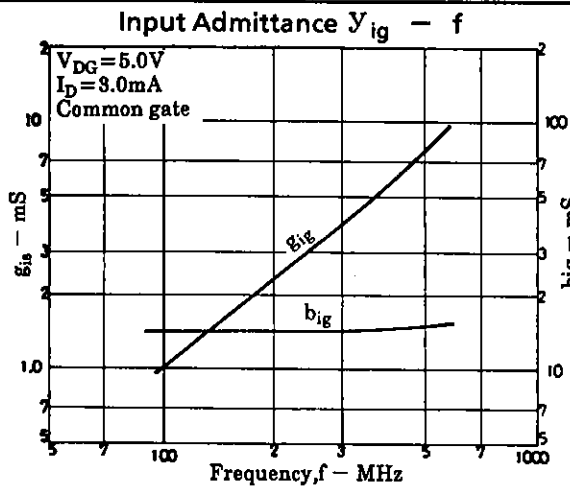
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